

Active

- ✱ L1: (24668) insulat\$3 adj layer and gate adj electrode and substrate
- ✱ L2: (62831) ((bit adj line) or bitline)
- ✱ L3: (2562) ((bit adj line) or bitline) with cover\$3
- ✱ L4: (21) 3 with isolation adj layer
- ✱ L5: (474263) 4 and contact plug
- ✱ L6: (10) 4 and contact adj plug
- ✱ L7: (4) 6 and buried
- ✱ Failed
- ✱ Saved
 - ✱ (8760) (257/295-313,903-908) CCLS.
 - ✱ (76340) DRAM
 - ✱ (3289) ((257/295-313,903-908) CCLS.) and DRAM
 - ✱ (21217) DRAM and insulat\$3
 - ✱ (6931) (DRAM and insulat\$3) and gate adj electrode.
 - ✱ (402) ((DRAM and insulat\$3) and gate adj electrode) and isolat\$3 adj layer
 - ✱ (74) (((DRAM and insulat\$3) and gate adj electrode) and isolat\$3 adj layer) and contact adj plug
 - ✱ (6) (((DRAM and insulat\$3) and gate adj electrode) and isolat\$3 adj layer) and buried adj contac

Favorites

Default speed: Highlight all hit items initially

5 and buried

	U	I	Document ID	Issue Date	Pages	Title	Current	Cur/Re	Inventor	S	C	P	2	3
1	r	r	US 20020149977 A1	20021017	9	Semiconductor memory	365/200		Oh, Jae-Hee	P	P	P	P	P
2	r	r	US 6620685 B2	20030916	8	Method for fabricating of 438/257	438/		Oh, Jae-Hee	P	P	P	P	P
3	r	r	US 6326295 B1	20011204	14	Method and structure for 438/622	257/		Figura, Thomas A.	P	P	P	P	P
4	r	r	US 6225208 B1	20010501	11	Method and structure for 438/622	257/		Figura, Thomas A.	P	P	P	P	P

Ready

NULM

L Number	Hits	Search Text	DB	Time stamp
1	24668	insulat\$3 adj layer and gate adj electrode and substrate	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:25
2	62831	((bit adj line) or bitline)	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:26
3	2562	((bit adj line) or bitline) with cover\$3	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:26
4	21	((bit adj line) or bitline) with cover\$3 with isolation adj layer	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:26
5	474263	((((bit adj line) or bitline) with cover\$3) with isolation adj layer) and contact plug	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:27
6	10	((((bit adj line) or bitline) with cover\$3) with isolation adj layer) and contact adj plug	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:27
7	4	(((((bit adj line) or bitline) with cover\$3) with isolation adj layer) and contact adj plug) and buried	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:27
-	8760	(257/295-313,903-908).CCLS.	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:13
-	76340	DRAM	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:13
-	3289	((257/295-313,903-908) CCLS.) and DRAM	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:13
-	21217	DRAM and insulat\$3	USPAT; US-PGPUB, EPO, JPO, DERWENT; IBM_TDB	2003/12/05 09:24
-	6931	(DRAM and insulat\$3) and gate adj electrode	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:15

-	402	((DRAM and insulat\$3) and gate adj electrode) and isolat\$3 adj layer	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:16
-	74	((((DRAM and insulat\$3) and gate adj electrode) and isolat\$3 adj layer) and contact adj plug	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:16
-	6	((((DRAM and insulat\$3) and gate adj electrode) and isolat\$3 adj layer) and buried adj contact adj plug	USPAT; US-PGPUB; EPO, JPO, DERWENT; IBM_TDB	2003/12/04 16:16